

# XP131A0526SR



## Power MOS FET

- ◆N-Channel Power MOS FET
- ◆DMOS Structure
- ◆Low On-State Resistance:  $0.026\Omega$  (max)
- ◆Ultra High-Speed Switching
- ◆SOP-8 Package

## Applications

- Notebook PCs
- Cellular and portable phones
- On-board power supplies
- Li-ion battery systems

## General Description

The XP131A0526SR is an N-Channel Power MOS FET with low on-state resistance and ultra high-speed switching characteristics.

Because high-speed switching is possible, the IC can be efficiently set thereby saving energy.

The small SOP-8 package makes high density mounting possible.

## Features

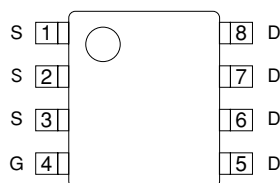
**Low on-state resistance** :  $R_{ds(on)}=0.017\Omega$  ( $V_{gs}=10V$ )  
 :  $R_{ds(on)}=0.026\Omega$  ( $V_{gs}=4.5V$ )

**Ultra high-speed switching**

**Operational Voltage** : 4.5V

**High density mounting** : SOP-8

## Pin Configuration

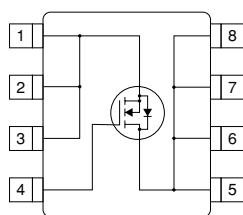


SOP-8  
(TOP VIEW)

## Pin Assignment

PIN NUMBER	PIN NAME	FUNCTION
1 ~ 3	S	Source
4	G	Gate
5 ~ 8	D	Drain

## Equivalent Circuit



N-Channel MOS FET  
(1 device built-in)

## Absolute Maximum Ratings

$T_a=25^\circ\text{C}$

PARAMETER	SYMBOL	RATINGS	UNITS
Drain-Source Voltage	$V_{dss}$	30	V
Gate-Source Voltage	$V_{gss}$	$\pm 20$	V
Drain Current (DC)	$I_d$	10	A
Drain Current (Pulse)	$I_{dp}$	30	A
Reverse Drain Current	$I_{dr}$	10	A
Continuous Channel Power Dissipation (note)	$P_d$	2.5	W
Channel Temperature	$T_{ch}$	150	$^\circ\text{C}$
Storage Temperature	$T_{stg}$	-55~150	$^\circ\text{C}$

Note: When implemented on a glass epoxy PCB

## Electrical Characteristics

### DC Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Drain Cut-off Current	Idss	Vds=30V, Vgs=0V			10	μA
Gate-Source Leakage Current	Igss	Vgs=±20V, Vds=0V			±1	μA
Gate-Source Cut-off Voltage	Vgs(off)	Id=1mA, Vds=10V	1.0		2.5	V
Drain-Source On-state Resistance (note)	Rds(on)	Id=5A, Vgs=10V			0.017	Ω
		Id=5A, Vgs=4.5V			0.026	Ω
Forward Transfer Admittance (note)	Yfs	Id=5A, Vds=10V		15		S
Body Drain Diode Forward Voltage	Vf	If=10A, Vgs=0V		0.8	1.1	V

Note: Effective during pulse test.

### Dynamic Characteristics

Ta=25°C

PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Input Capacitance	Ciss	Vds=10V, Vgs=0V f=1MHz		1350		pF
Output Capacitance	Coss			800		pF
Feedback Capacitance	Crss			300		pF

### Switching Characteristics

Ta=25°C

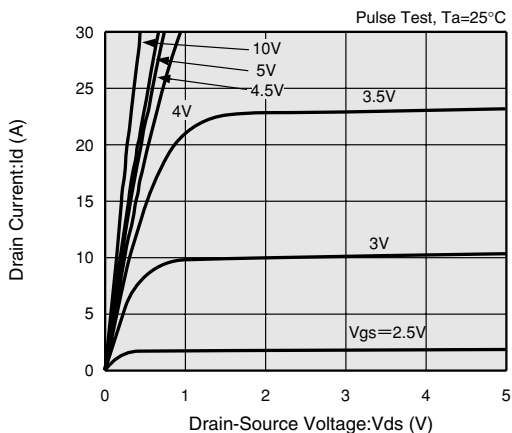
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS	
Turn-on Delay Time	td (on)	Vgs=5V, Id=5A Vdd=10V		20		ns	
Rise Time	tr			35		ns	
Turn-off Delay Time	td (off)				35		ns
Fall Time	tf				20		ns

### Thermal Characteristics

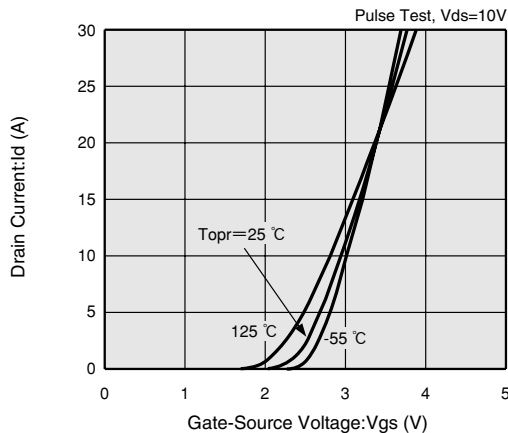
PARAMETER	SYMBOL	CONDITIONS	MIN	TYP	MAX	UNITS
Thermal Resistance (channel-ambience)	Rth (ch-a)	Implement on a glass epoxy resin PCB		50		°C/W

## Typical Performance Characteristics

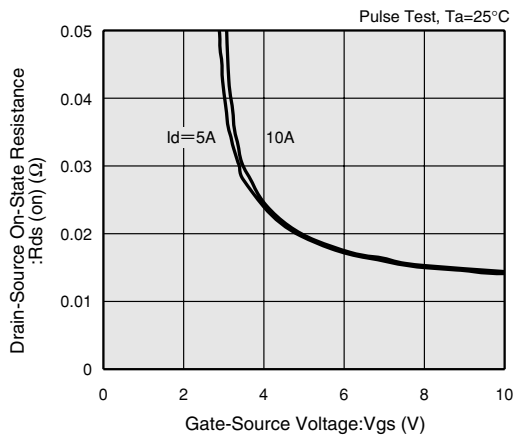
DRAIN CURRENT vs. DRAIN-SOURCE VOLTAGE



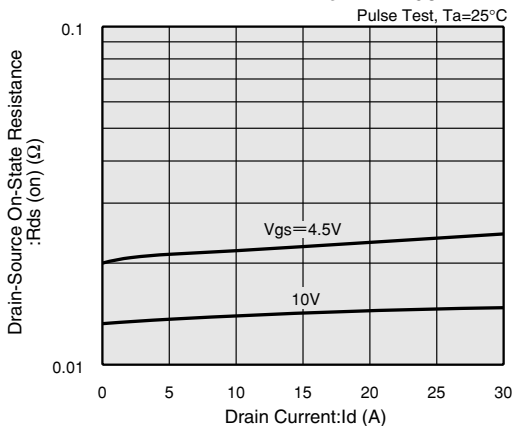
DRAIN CURRENT vs. GATE-SOURCE VOLTAGE



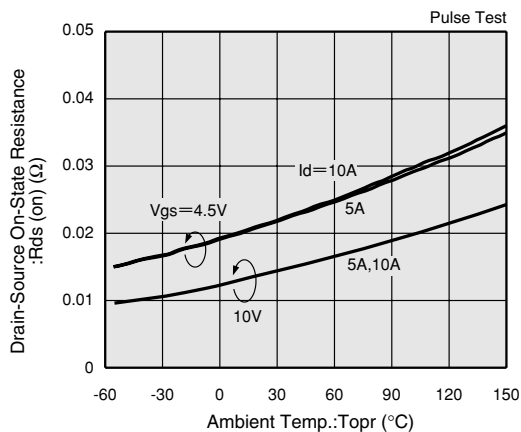
DRAIN-SOURCE ON-STATE RESISTANCE vs. GATE-SOURCE VOLTAGE



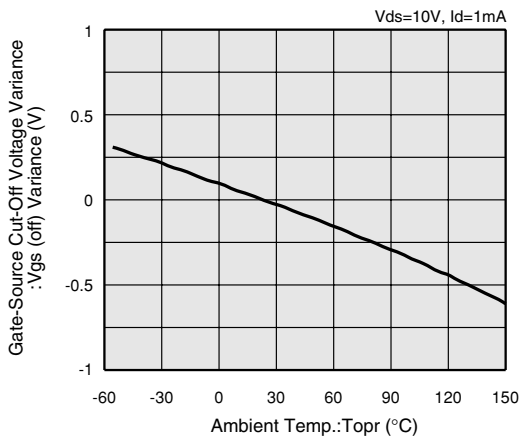
DRAIN-SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT



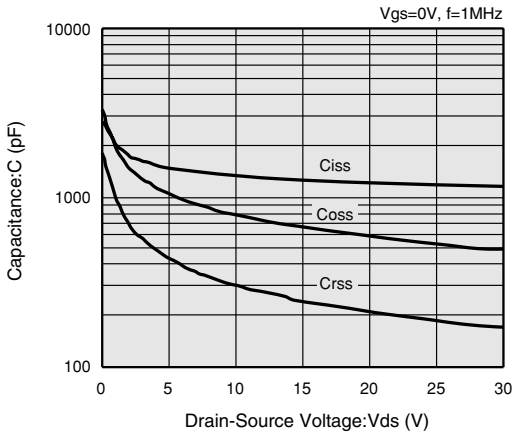
DRAIN-SOURCE ON-STATE RESISTANCE vs. AMBIENT TEMPERATURE



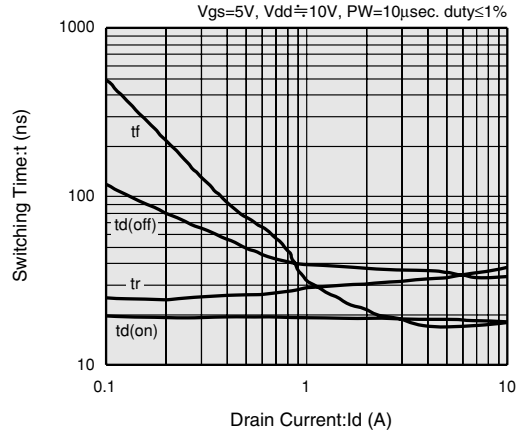
GATE-SOURCE CUT-OFF VOLTAGE VARIANCE vs. AMBIENT TEMPERATURE



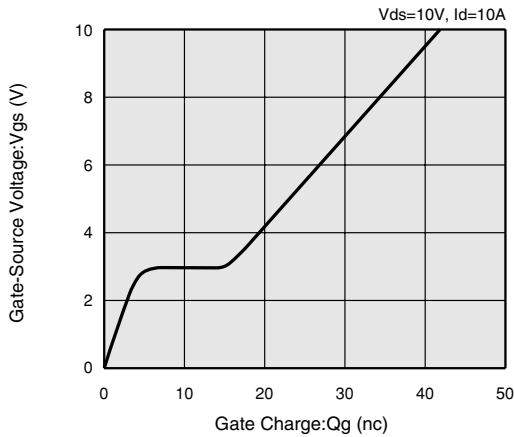
CAPACITANCE vs. DRAIN-SOURCE VOLTAGE



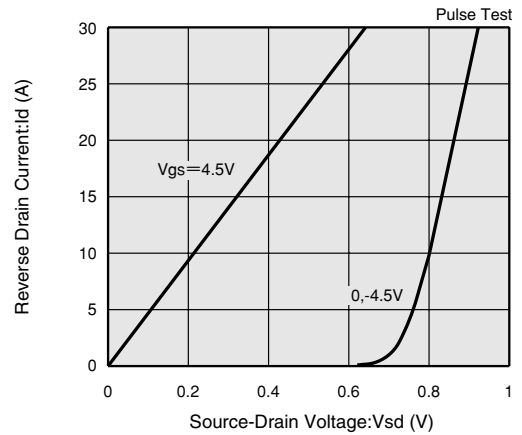
SWITCHING TIME vs. DRAIN CURRENT



GATE-SOURCE VOLTAGE vs. GATE CHARGE



REVERSE DRAIN CURRENT vs. SOURCE-DRAIN VOLTAGE



STANDARDIZED TRANSITION THERMAL RESISTANCE vs. PULSE WIDTH

